Germanium PNP Transistor

2N173

40/60V / 15A

DATASHEET

OEM - Delco

Source: Delco Power Transistors 1958

DELCO RADIO DIVISION

GENERAL MOTORS CORPORATION KOKOMO, INDIANA

2N173

POWER TRANSISTOR

Distributed in the U.K. by

ENGINEERING DATA SHEET SUPERSEDES ALL PREVIOUS DATA SHEETS

November 4, 1958

AC-DELCO DIVISION OF GENERAL MOTORS LTD.

DUNSTABLE, BEDFORDSHIRE

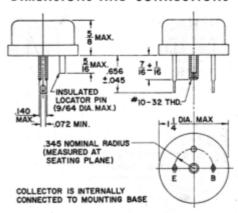
GENERAL DESCRIPTION

The improved Delco Radio Type 2N173, is a P-N-P germanium power transistor designed for general use with a 12 volt power supply. It is characterized by a new, higher maximum emitter current of 15 amperes, a maximum collector voltage of 60 volts and a thermal resistance below 1°C per watt. A low saturation resistance will give high efficiency in switching applications. The distortion is low both in Class A operaton and in class AB operation with matched pairs.

The case is hermetically sealed. The collector and the case are electrically connected.

The Delco 2N173 transistors will be supplied either in single units or in matched pairs.

DIMENSIONS AND CONNECTIONS



ABSOLUTE MAXIMUM RATINGS

Collector diode voltage V_{CB}	30	volts	Maximum junction temperature Continuous	95°C
Emitter diode voltage VEB 4		volts	Intermittent	100°C
		amp.	Minimum junction temperature	-65°C

ELECTRICAL CHARACTERISTICS (T = 25°C)

	Min.	Typical	Max.	
Collector diode current I _{co} (V _{cm} = -2 volts)		100		microamp
Collector diode current I _{CO} (V _{CB} = -60 volts)		2	8	ma
Emitter diode current Igo (VgB = -40 volts)		1	8	ma
Current gain (VCE = -2 volts, Ic = 5 amps)	35		- 70	
Current gain (Vck = -2 volts, Ic = 12 amps)		25		
Base voltage VER (VEC = -2 volts, IC = 5 amps)		0.65		volts
Floating potential VEB (VCB = -80 volts, IE = 0)		0.15	1	volts
Saturation voltage V _{EC} (I _B = 2 A, I _C = 12 amp)		0.3	1	volts
Collector to emitter voltage V_{CE8} ($I_C = 300$ ma d.c., $V_{E8} = 0$)	50			volts
Collector to emitter voltage V_{CEO} ($I_C = 300$ ma d.c., $I_B = 0$)		50		volts
Common emitter current amplification cutoff frequency				4.0
$(I_C = 5 \text{ amp, } V_{EC} = -6 \text{ volts})$		10		ke.
Rise time ("on" $I_C = 12$ Adc, $I_B = 2$ amp, $V_{CR} = -12$ volts)		15		micro sec.
Fall time ("off" $I_C = 0$, $V_{EB} = -6$ volts, $R_{EB} = 10\Omega$)		15		micro sec.

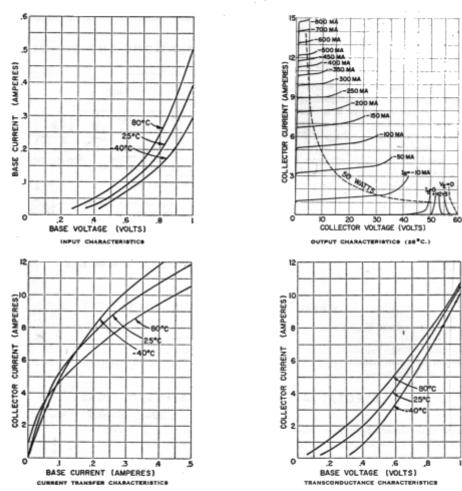
THERMAL CHARACTERISTICS

Thermal resistance (junction to mounting base)	.7	1	°C/watt
Thermal capacity for pulses in the 1 to 10 millisecond range	.075		watt sec/°C

2N173

DELCO RADIO DIVISION
GENERAL MOTORS CORPORATION

TYPICAL CHARACTERISTICS, COMMON EMITTER



MECHANICAL DATA

The 2N173 transistor has been designed to pass the following environmental tests: (The numbers refer to paragraphs of MIL-T-19500) Temperature Cycling (4.6.24), Glass Strain (4.6.25), Moisture Resistance (4.6.26), Shock (4.6.28), Vibration Fatigue (4.6.30), Vibration Noise (4.6.31), and Reduced Pressure (15 mm of mercury) (4.6.32). Maximum recommended torque on the mounting stud is twelve inch-pounds.

DELCO RADIO DIVISION GENERAL MOTORS CORPORATION KOKOMO, INDIANA

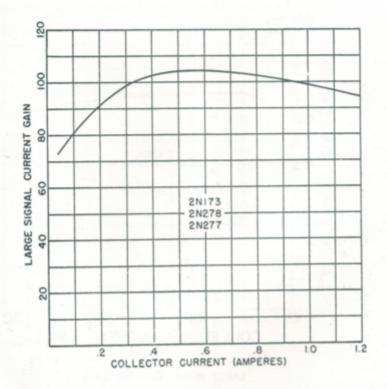
LARGE SIGNAL CURRENT GAIN AT LOW COLLECTOR CURRENTS

APPLICATION NOTE 11-A

January 1, 1958

LARGE SIGNAL CURRENT GAIN AT LOW COLLECTOR CURRENTS

Many circuits using Delco power transistors draw currents less than one ampere. Because of the wide collector current range of the transistors, our engineering data sheets do not show in detail what typical current gain to expect at low values of collector current. The following graph shows the typical current gain of three of our transistors, when the collector current is less than 1.2 amperes.



LARGE SIGNAL CURRENT GAIN AT LOW COLLECTOR CURRENTS